

ECE 124a/256c



VLSI RC(L) Interconnect Models

Forrest Brewer

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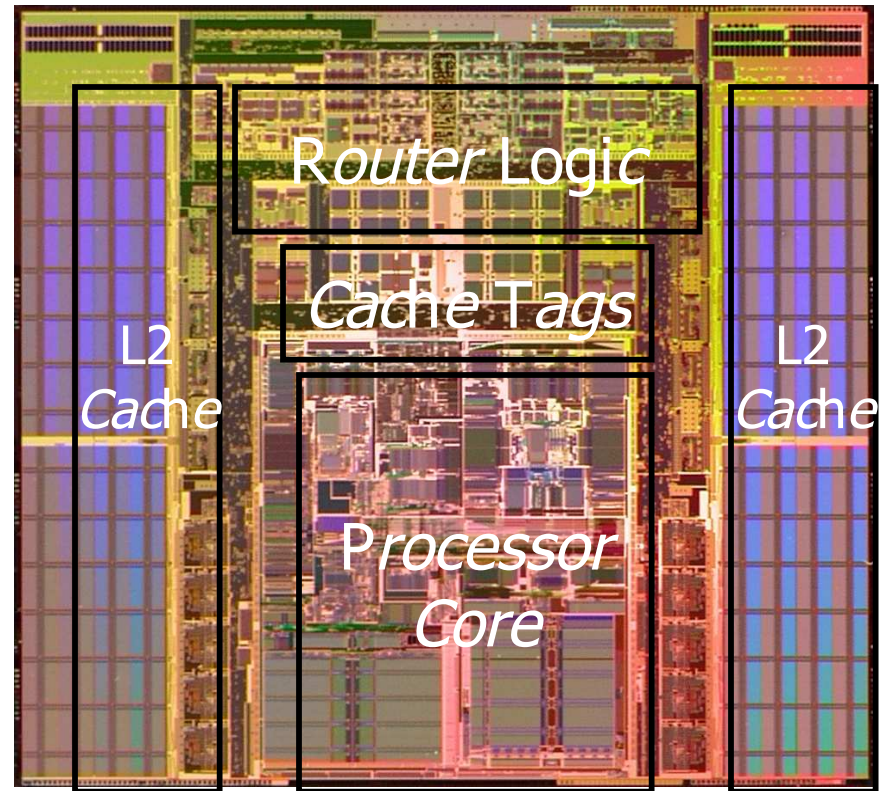


Readings

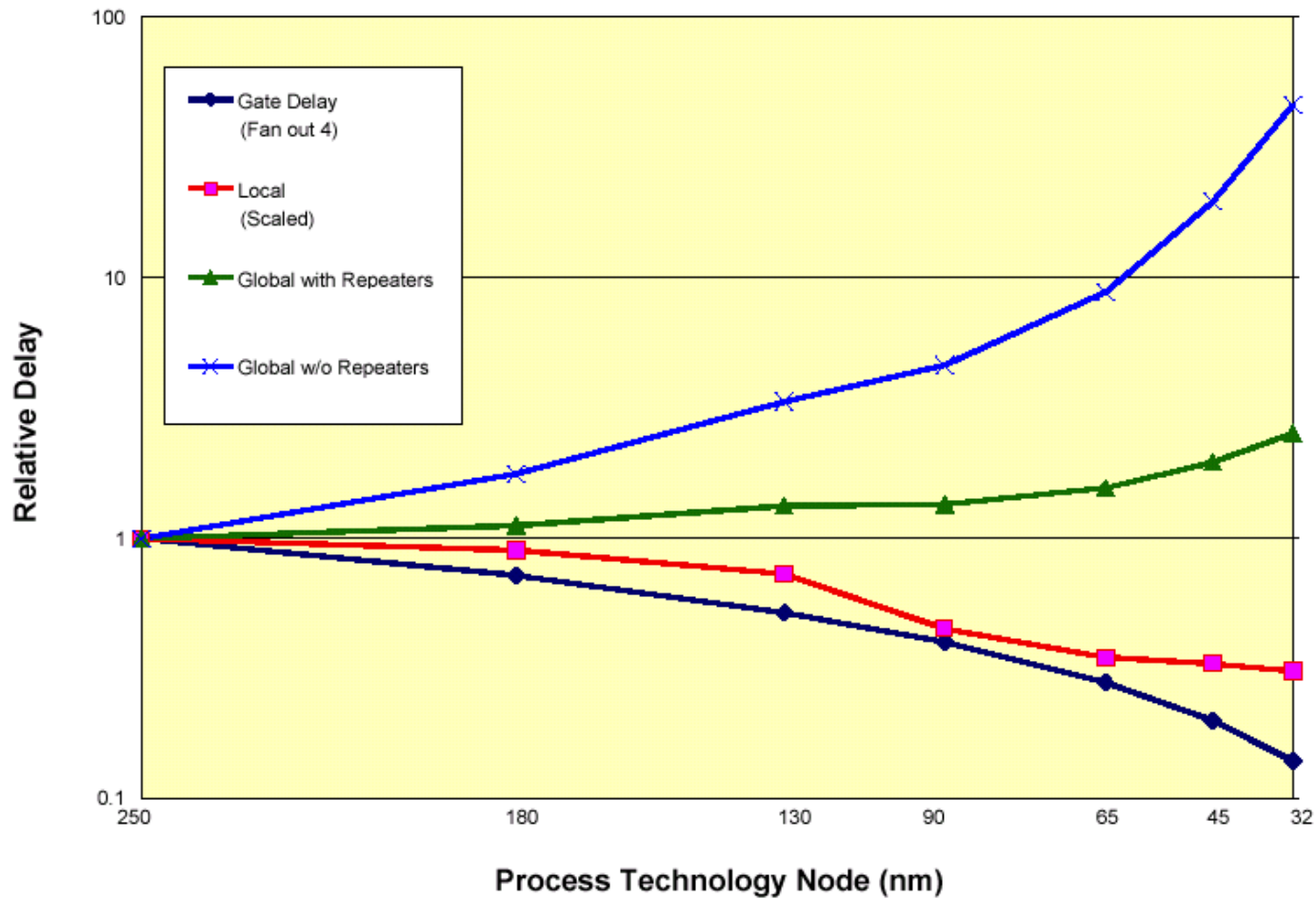
- H. B. Bakoglu, “*Circuits interconnects and packaging for VLSI*” , Addison Wesley
- W. J. Dally and J. W. Poulton, “*Digital Systems Engineering*” , Cambridge Press
- J. M. Rabaey, “*Digital Integrated circuits : A design perspective*” , Prentice Hall

Components of VLSI system

- Logic
 - Functional Block
 - Logic Gates
 - Transistors
- Interconnects
 - Power/ground and Clock
 - Inter-block Signals
 - Intra-block Signals



Delay with technology scaling



This figure is from the ITRS Roadmap on interconnects

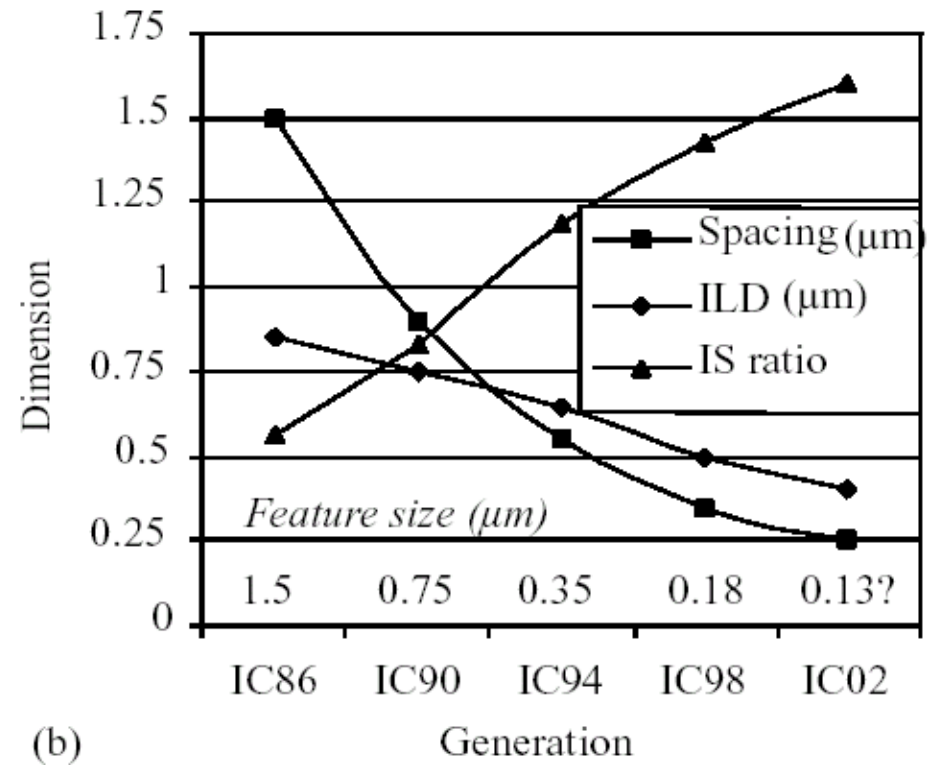
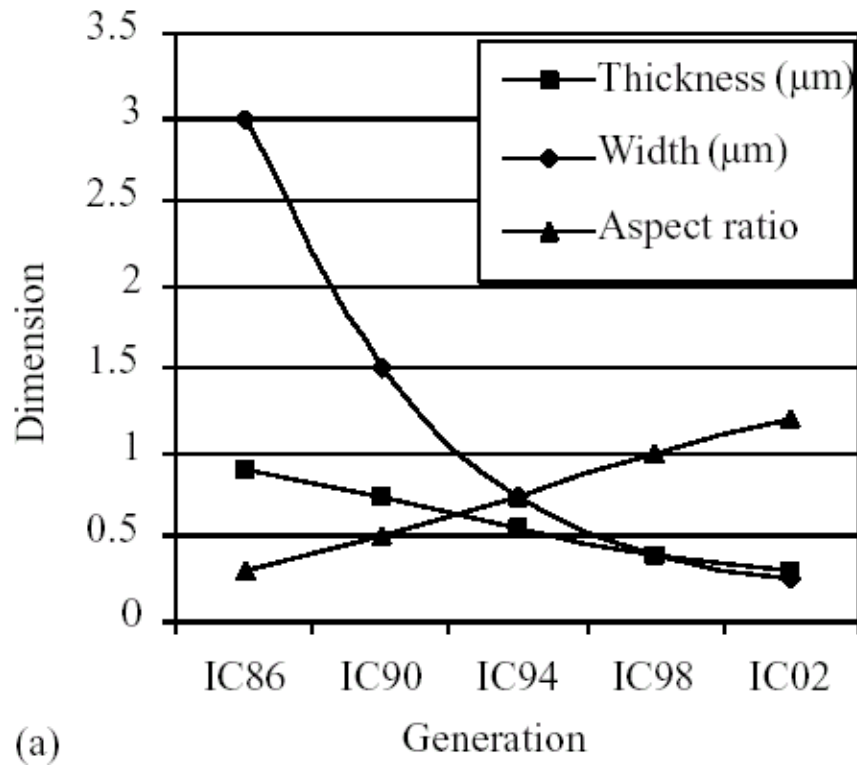


NTRS Roadmap

Year Parameter	2003	2004	2005	2008	2011	2014
Technology(nm)	120	110	100	70	50	35
# of Transistors	95.2M	145M	190M	539M	1523M	4308M
Clock Frequency	1724 MHz	1857 MHz	2000 MHz	2500 MHz	3000 MHz	3600 MHz
Chip Area (mm ²)	372	372	408	468	536	615
Wiring Levels	8	8	8-9	9	9-10	10
Pitch(L/I/G)(nm)	330/420/690	295/375/620	265/340/560	185/240/390	130/165/275	95/115/190
A/R (L/I/G)	1.6/2.2/2.8	1.6/2.3/2.8	1.7/2.4/2.8	1.9/2.5/2.9	2.1/2.7/3.0	2.3/2.9/3.1
Dielectric Const.	2.2-2.7	2.2-2.7	1.6-2.2	1.5	<1.5	<1.5

This data is from the ITRS Roadmap on interconnects

Interconnect dimension trends



These figures are derived from *Design of High-Performance Microprocessor Circuits*, A. Chandrakasan, W. Bowhill, F. Fox, IEEE, 2001



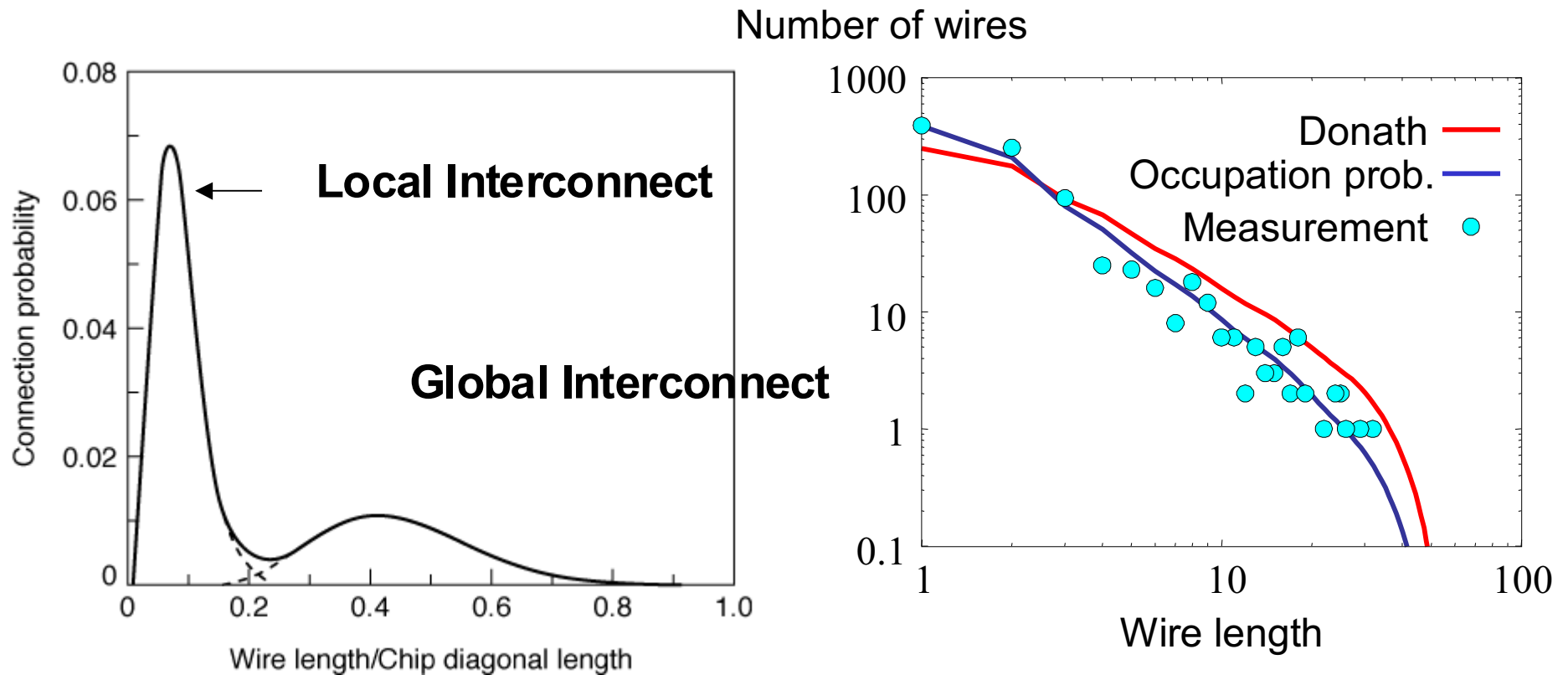
Rent's rule

- Rent's rule relates the I/O requirement to the number of gates as :

$$N_p = K_p N_g^\beta$$

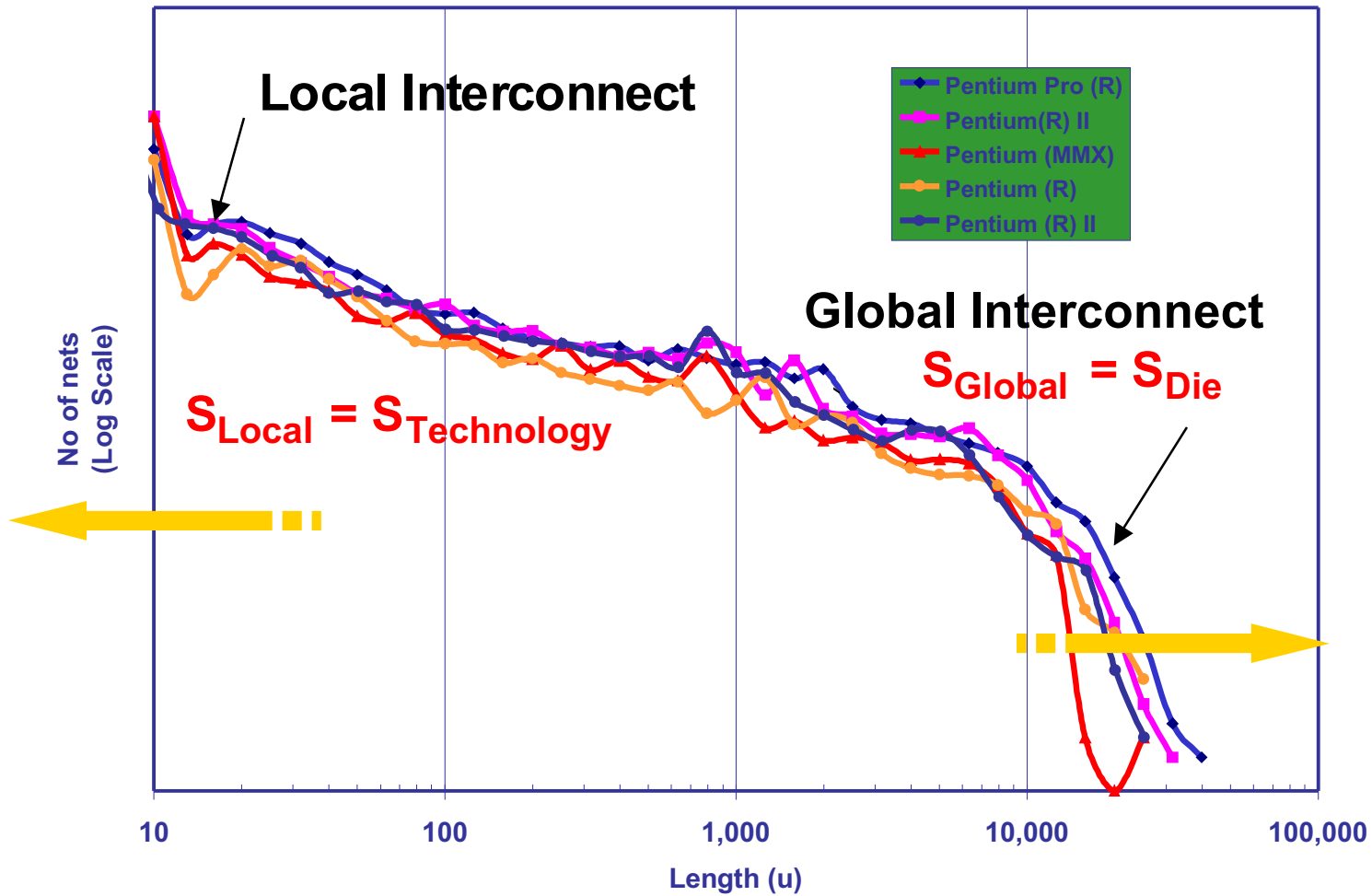
- As technology scales number of gates in a given area is increasing.
- More routing is required as technology scales.

Nature of the interconnect

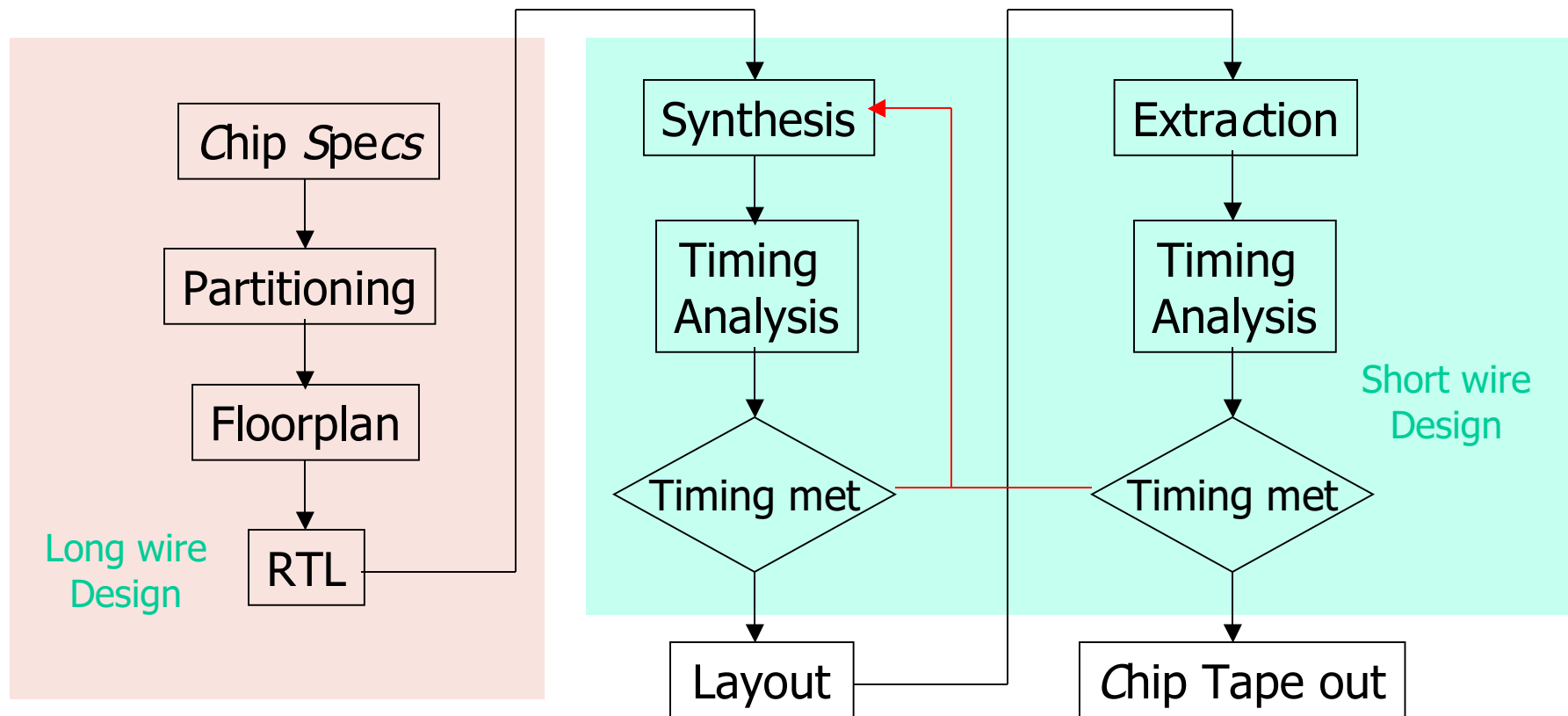


These figures are derived from *Digital integrated circuit – a design perspective*, J. Rabaey Prentice Hall and a tutorial in SLIP by Dirk Stroobandt respectively

Microprocessor Interconnect

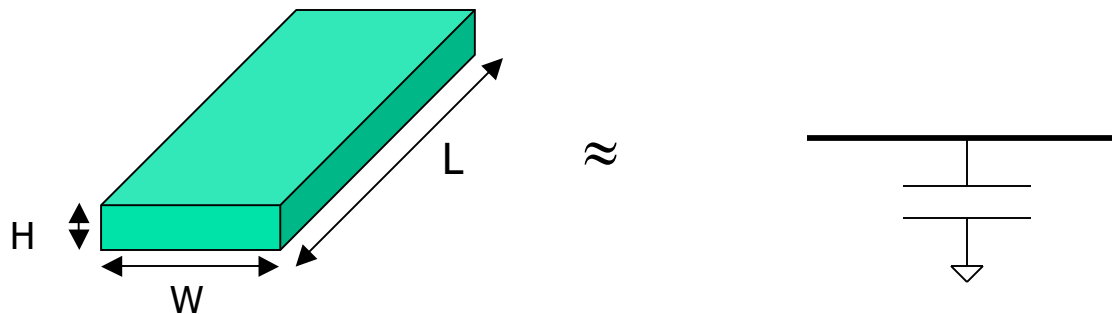


VLSI Design Cycle



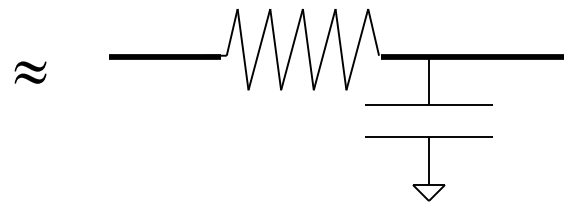
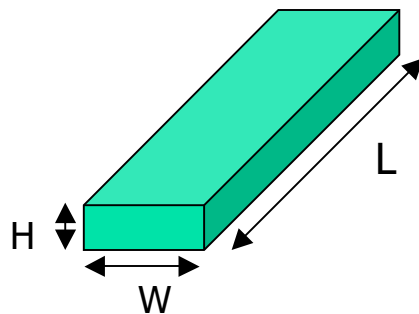
Early models

- Wire width \propto feature size
- Older technology had wide wires
- More cross-section area implies less resistance and more capacitance.
- Model wire only with capacitance



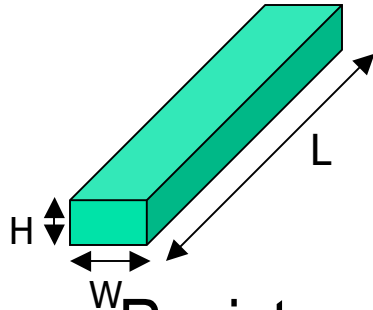
However...

- With scaling, width of wire reduced.
- Resistance of the wire no longer negligible.
- Wire not very long and a lumped RC is good enough approximation.





Interconnect Resistance



$$R = \frac{\rho L}{HW}$$

- Ohm's Law: Resistance of wire \propto wire length (L) and $1/\propto$ cross-section(HW)
- ρ (resistivity) is the property of the material.



Sheet Resistance

- Wire height (H) is constant for a technology.
- Sheet resistance (R_q) is constant for each metal layer.
- Calculation of wire resistance is easy : multiply R_q by L/W

$$R = R_q \frac{L}{W}$$

with

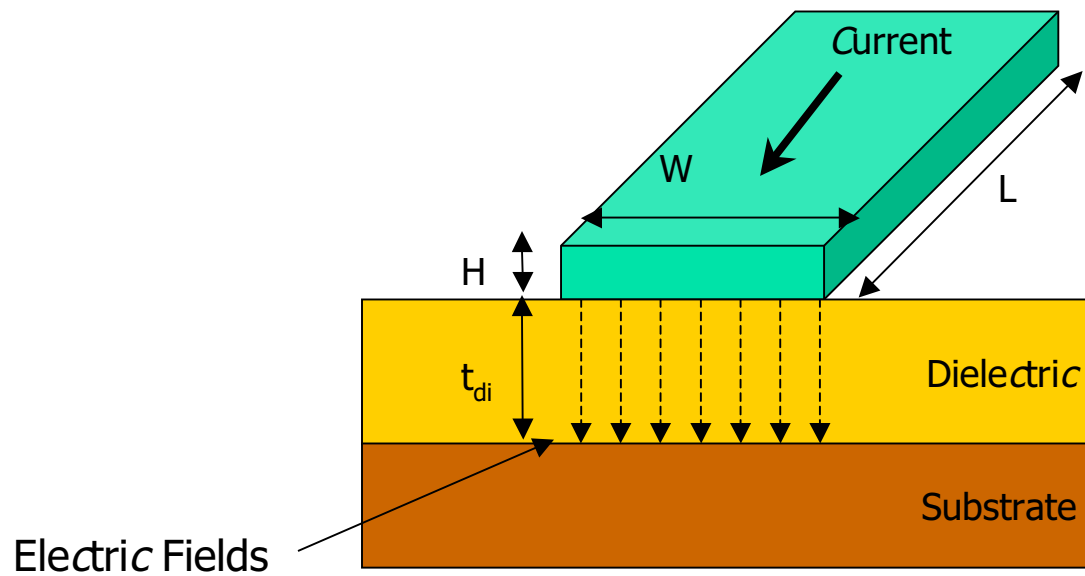
$$R_q = \frac{\rho}{H}$$



Interconnect Capacitance

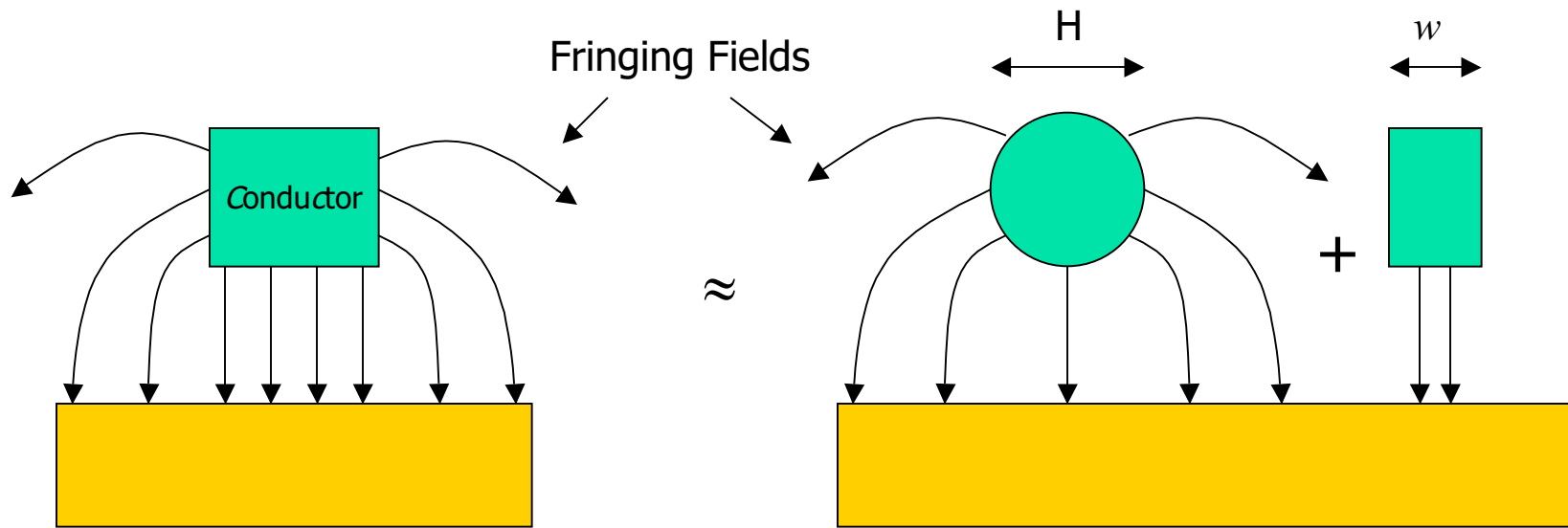
- Capacitance of a wire = ϵ (Shape, Distance to surrounding wires, Distance to the substrate)
- Estimating Capacitance is a matter of determining where the field lines go.
- To get an accurate estimate electric field solvers (2D or 3D) are used. E.g. Fastcap or Rafael
- When in doubt, typical wires have self capacitance between 1 and 3 pf/cm

Area Capacitance



$$C_{\text{int}} = \frac{\epsilon_{di}}{t_{di}} WL$$

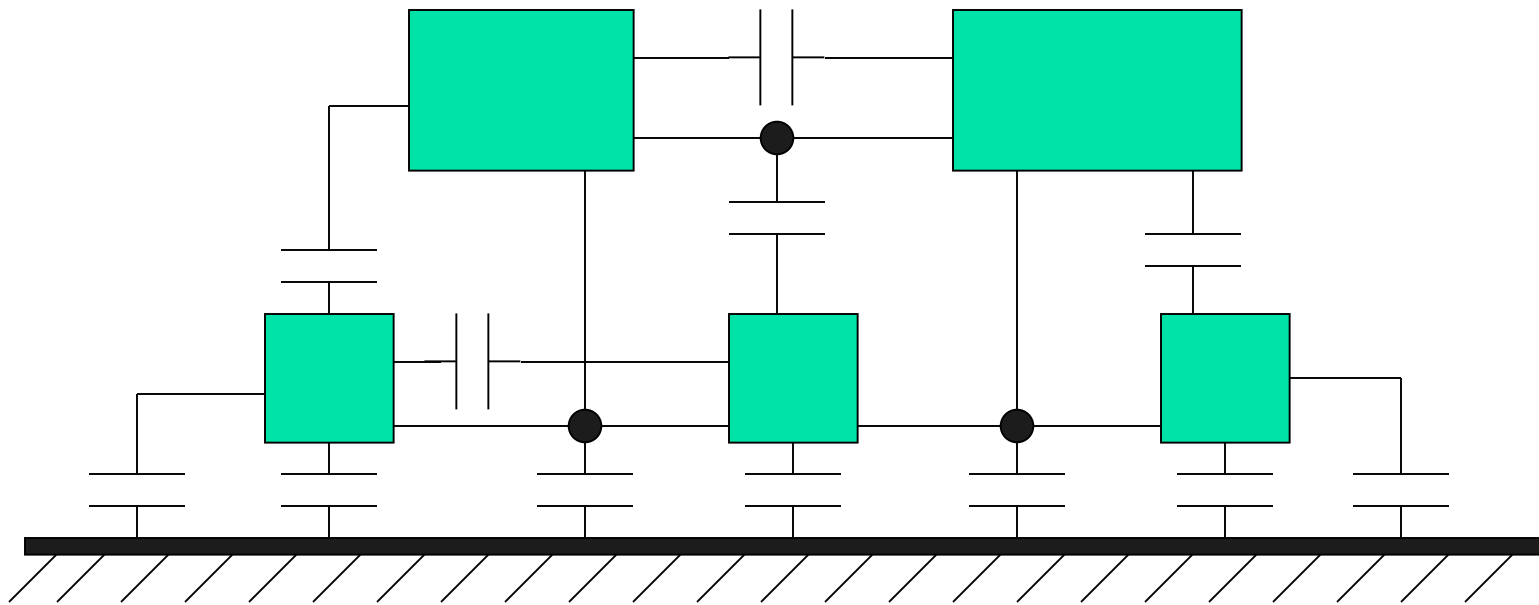
Fringing Capacitance



$$C_{wire} = C_{pp} + C_{fringe} = \frac{2\pi\epsilon_{di}}{\log(4t_{di}/H + 2)} + \frac{w\epsilon_{di}}{t_{di}}$$

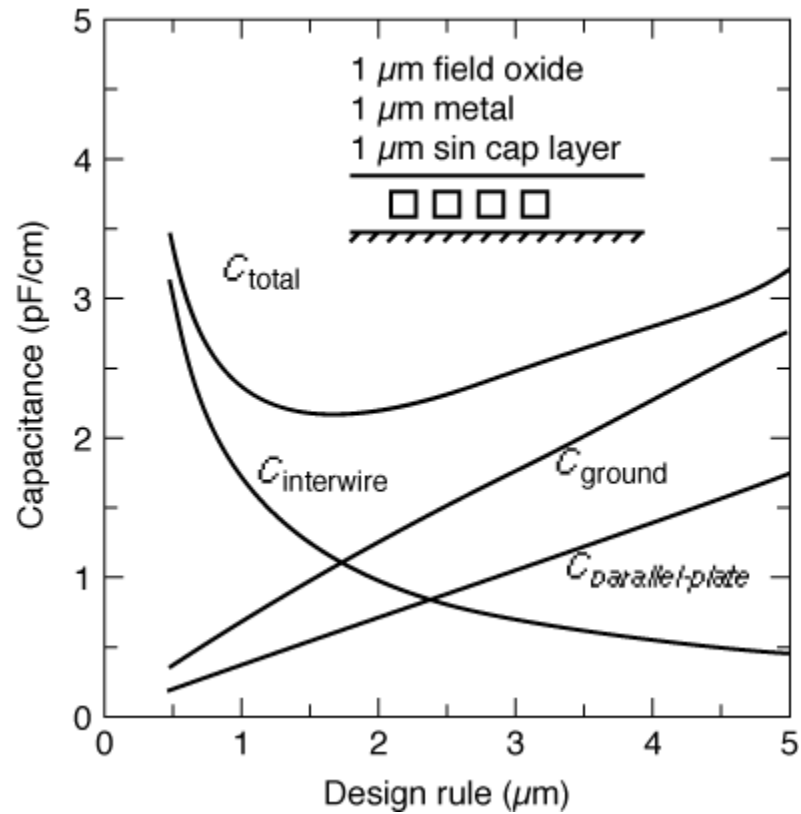
$$w \approx W - H/2$$

Detailed Picture



Is this much of detail required... How to compute this?

Interwire Capacitance



(from [Bakoglu89])

Wiring Capacitances (0.18 μm)

Capacitance	N+	P+	poly	m1	m2	m3	m4	m5	m6
substrate	998+244	1152+201	103+21	39+38	19+61	13+55	9+43	8+25	3
N+ active			8655	54	21	14	11	10	9
P+ active			8324						
poly				64+69	18+39	10+29	7+24	6+21	5+19
m1					44+61	16+35	10+31	7+23	5+21
m2						38+54	15+37	9+27	7+24
m3							40+56	15+34	9+31
m4								37+58	14+40
m5									36+61

Units: First number is area component (af/ μm^2), second is fringing component (af/ μm)



How to use fringe capacitance tables

- Estimation of wire Capacitance
 - Where do field lines terminate?
 - What fraction go where?
- E.g. 1cm of M1 over substrate: $39\text{af}/\mu\text{m}^2$, $38\text{af}/\mu\text{m}$ fringe
 - If 200nm wide = $0.2\mu\text{m}$, $0.2\mu\text{m} * 10,000\mu\text{m} = 2,000 * 39\text{af} = 78\text{fF}$
 - 1cm = 10,000 μm , fringe on both sides: $2 * 38\text{af} * 10,000 = 760\text{fF}$
 - Total = 848fF/cm
- Over Poly 64aF, 69aF – nearly doubles (half the distance to conductor)



Importance of Resistance

- Delay of wire \propto to the resistance of the wire.
- Resistance means ohmic (IR) drop along the wire, reduces noise margin.
- IR drop a significant problem in the power lines where current density is high.
- Keep wires short, to reduce resistance.
- Contact resistance makes them vulnerable to electromigration.



Metal Resistivity

Material	ρ ($\Omega\text{-m}$)
Silver (Ag)	1.6×10^{-8}
Copper (Cu)	1.7×10^{-8}
Gold (Au)	2.2×10^{-8}
Aluminum (Al)	2.7×10^{-8}
Tungsten (W)	5.5×10^{-8}

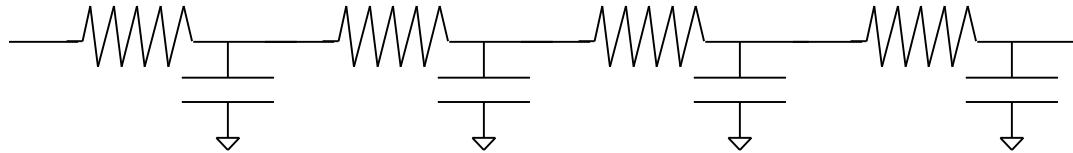


Importance of capacitance

- Delay of the wire is proportional to the capacitance charged.
- More capacitance means more dynamic power.
- Capacitance an increasing source of noise (coupling).
- Coupling make delay estimation hard.

Distributed model

- Wire can be modeled as a distributed RC line.



- As the number of elements increase distributed model becomes more accurate.
- For practical purposes wire-models with 5-10 elements are used to model the wire.

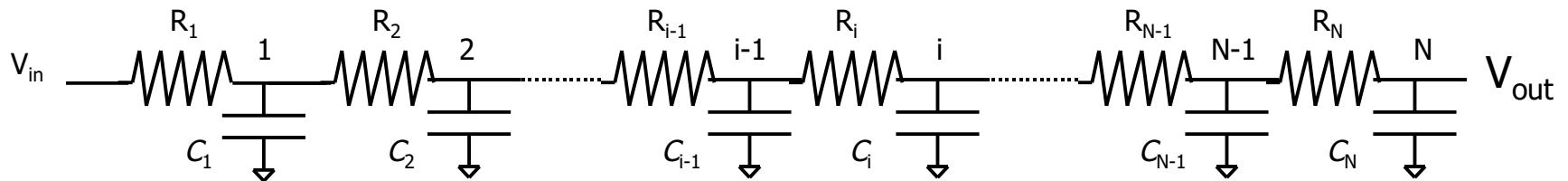


Elmore Delay...

- First order time constant at node is a sum of RC components.
- All the upstream resistances are taken into account.
- Thus each node contributes to the delay.
- Amount of contribution is the product of the cap at the node and the amount of resistance from source to the node.

Delay in distributed RC line

- Elmore analyzed the distributed model and came up with the figures for delay.



$$\tau_N = \sum_{i=1}^N R_i \sum_{j=i}^N C_j = \sum_{i=1}^N C_i \sum_{j=1}^i R_j$$

Elmore derived this equation in 1948 way before VLSI !!!



Wire Model

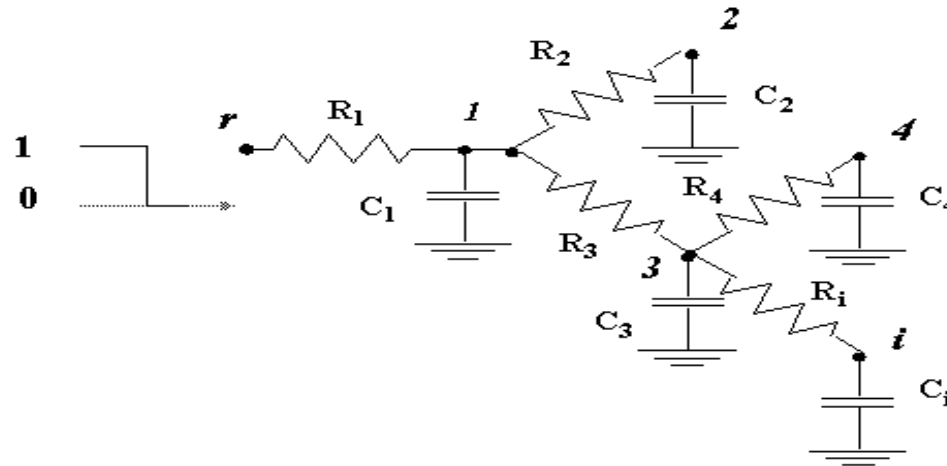
Assume: Wire modeled by N equal-length segments

$$\tau_{DN} = \left(\frac{L}{N}\right)^2 (rc + 2rc + \dots + Nrc) = (rcL^2) \frac{N(N+1)}{2N^2} = RC \frac{N+1}{2N}$$

For large values of N:

$$\tau_{DN} = \frac{RC}{2} = \frac{rcL^2}{2}$$

Generalized Elmore delay



$$\int_0^{\infty} v_i(t) dt = \sum_{k=1}^N C_k V_k(0) R_{i,k}$$

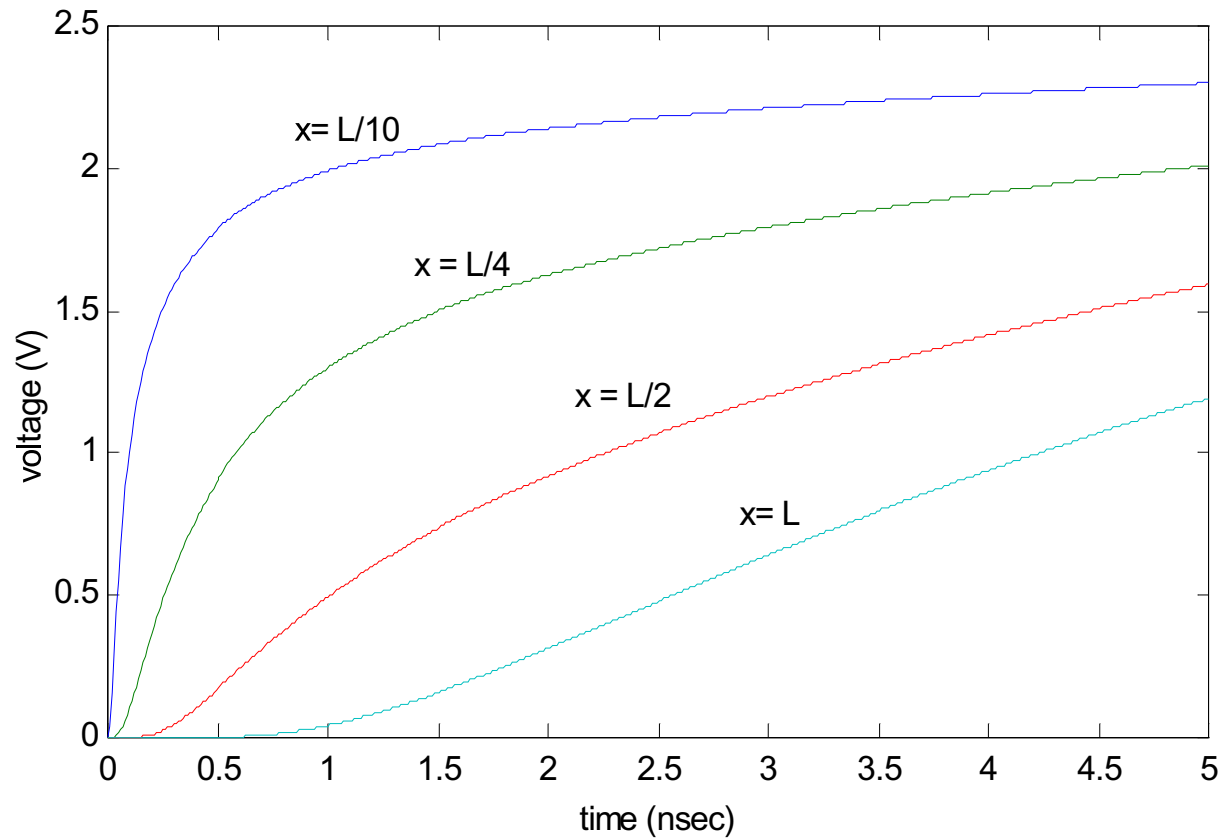
with

$$R_{i,k} = \sum R_j \Rightarrow (R_j \in [\text{path}(i \rightarrow r) \cap \text{path}(k \rightarrow r)])$$

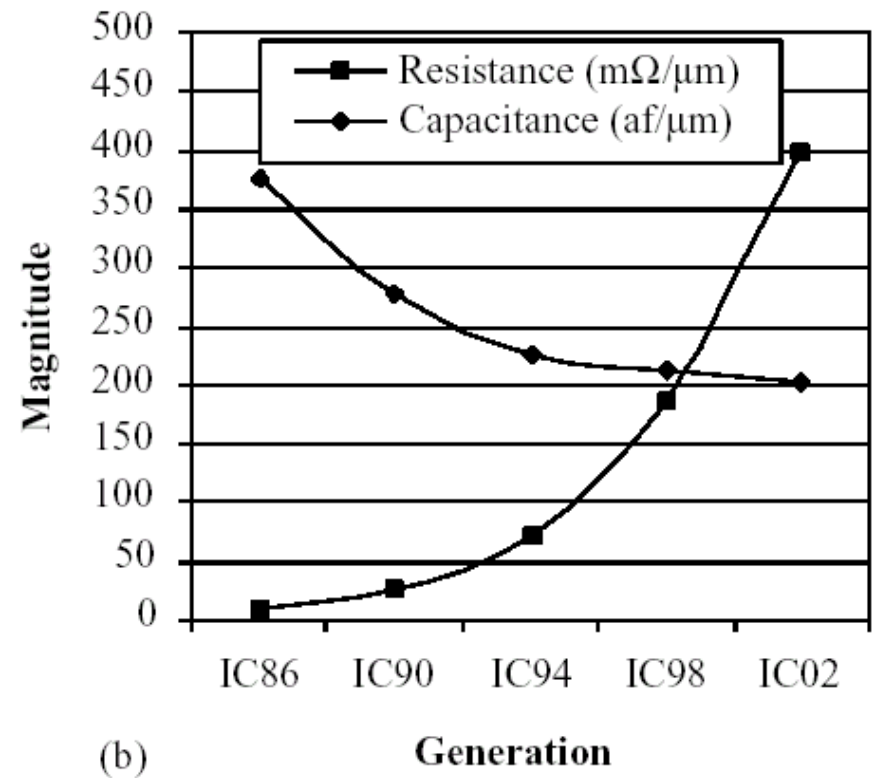
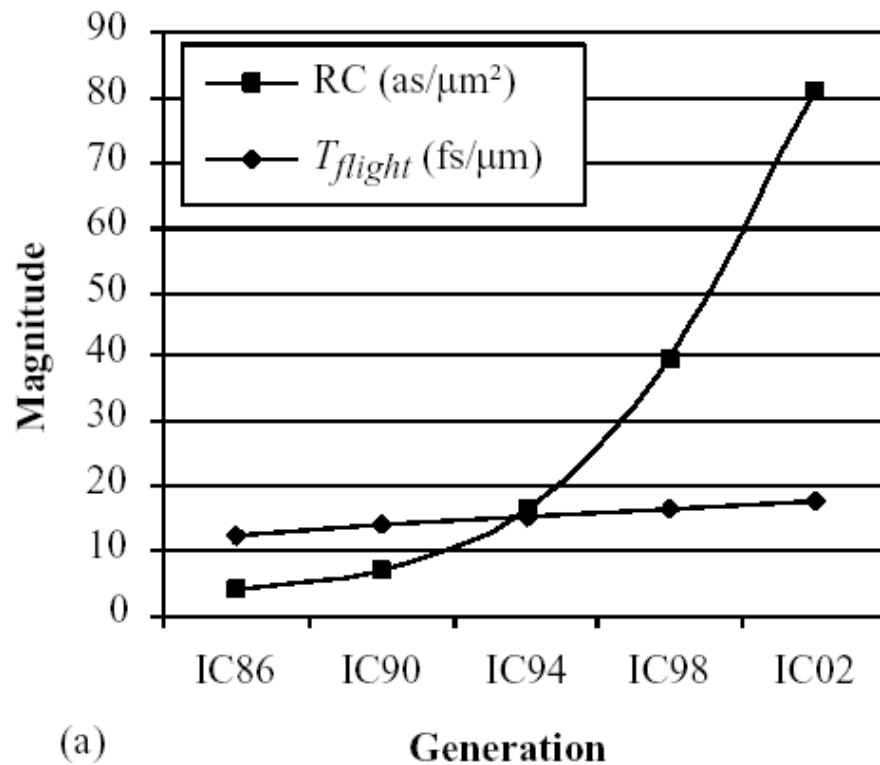
Rubinstein, Penfield and Horowitz generalized Elmore delay

This figure is derived from *Digital integrated circuit – a design perspective*, J. Rabaey Prentice Hall

Step-response of RC wire as a function of time and space



RC and flight-time

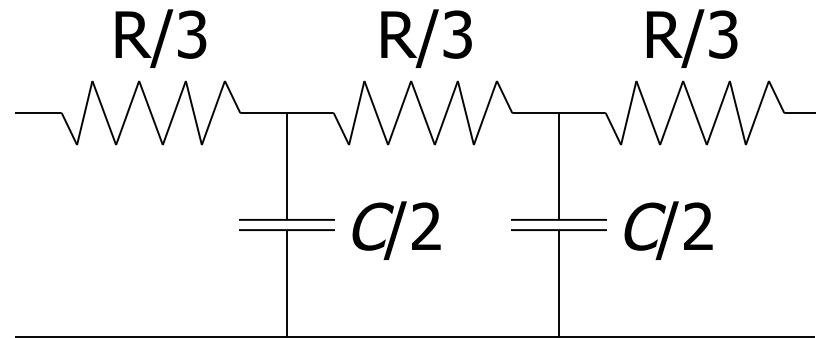


for a wide bus above a plane and beneath orthogonally routed layer

These figures are derived from *Design of High-Performance Microprocessor Circuits*, A. Chandrakasan, W. Bowhill, F. Fox, IEEE, 2001

Pi Model

- Pi Model of wire:



- Elmore Delay = $RC/3 + RC/6 = RC/2$ agrees with distributed model RC
- Pi Model is often used in Spice instead of large number of segments as a reasonable approximation of distributed RC

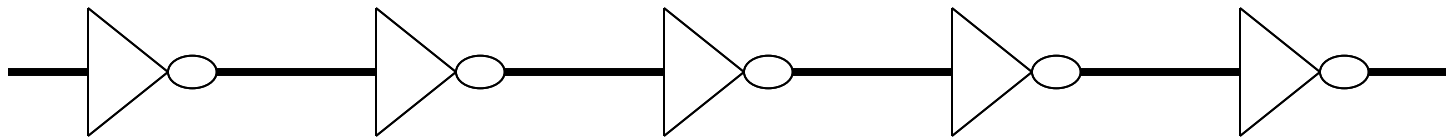
Driving an RC-line

$$\tau_D = R_s C_w + \frac{R_w C_w}{2} = R_s C_w + 0.5 r_w c_w L^2$$

$$t_p = 0.69 R_s C_w + 0.38 R_w C_w$$

- Delay for FET driven distributed RC – R_s is equivalent source resistance (usually assumed $R_s = V_{dd}/(2 I_{sat})$)
- RC gives delay for $\exp^{(-1)}$ change in output
- Scale time by $\ln(2) = 0.69$ to get typical 50% CMOS gate threshold

Repeaters



- Repeaters are buffers or inverters inserted at regular intervals.
- Delay linearly proportional to the wire length
- Questions to be answered – Where and how big should the repeaters be ?



Repeater placement

- Delay of the interconnect is typically optimum when

$$\text{Delay}_{\text{wire}} = \text{Delay}_{\text{buffer}}$$

- Closed form solutions for Repeater Number and Sizing
 - Bakoglu and Meindl, 1985 (Classical)
 - Adler and Friedman, 1998 (considering inductance)
 - Nalamalpu and Burleson, 2000 (ramped waveforms)
 - Chen Marek-Sadowska, Brewer, 2003 (short channel timing)
 - Cong, 2004 (tapered wires)



Bakoglu and Meindl

- For a wire with k repeaters each of size h times minimum size inverter is given by:

$$T_{50\%} = k \left[0.7 \frac{R_o}{h} \left(\frac{C_{\text{int}}}{k} + hC_o \right) + \frac{R_{\text{int}}}{k} \left(0.4 \frac{C_{\text{int}}}{k} + 0.7hC_o \right) \right]$$



Bakoglu and Meindl...

- By setting $dT/dk = 0$ and $dT/dh = 0$, optimal values for k and h are obtained

$$k = \sqrt{\frac{0.4R_{\text{int}}C_{\text{int}}}{0.7R_oC_o}} \quad h = \sqrt{\frac{R_oC_{\text{int}}}{R_{\text{int}}C_o}}$$

- Substituting these back, delay is given by

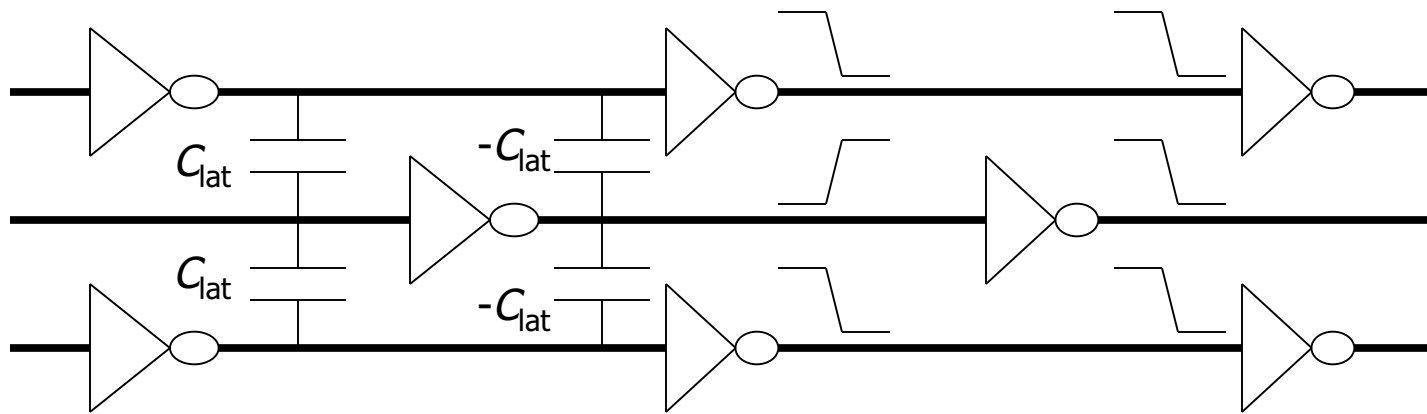
$$T_{50\%} = 2.5\sqrt{R_oC_oR_{\text{int}}C_{\text{int}}}$$



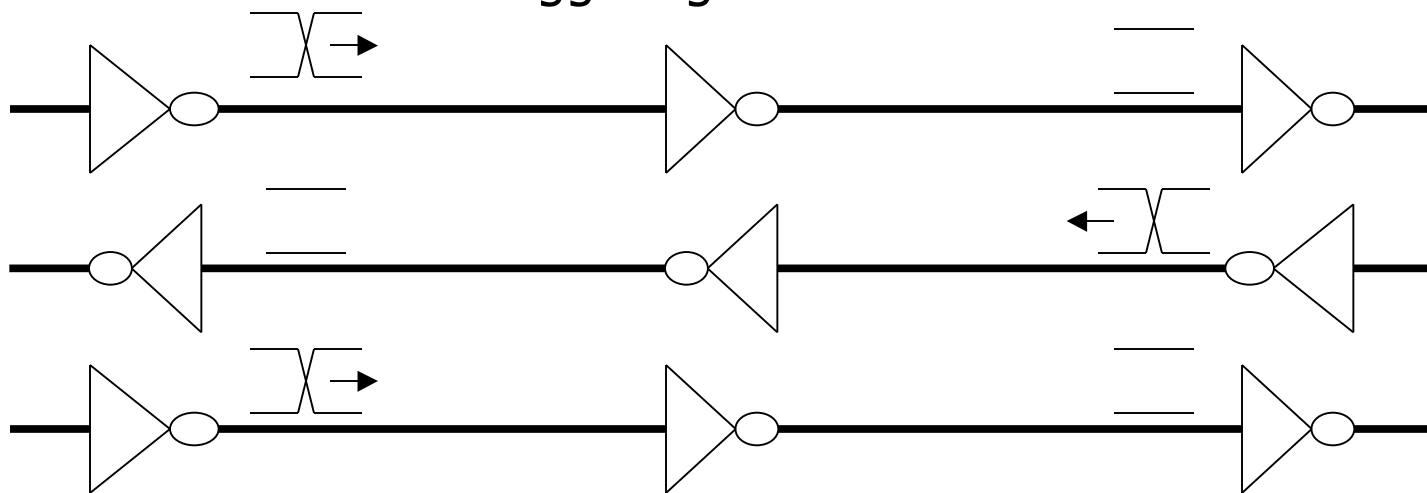
Optimization: Lagrange Multipliers

- A general technique for multi-dimensional optimization
- Problem: A function $f(x_1, x_2, \dots, x_n)$ to maximize subject to several constraints: $g_1(x_1, x_2, \dots, x_n) = 0$, $g_2(x_1, x_2, \dots, x_n) = 0$, ..., $g_m(x_1, x_2, \dots, x_n) = 0$ where $m < n$.
- Solution: $\nabla f = \lambda_1 \nabla g_1 + \lambda_2 \nabla g_2 + \dots + \lambda_m \nabla g_m$
- The n -dimensional equation above plus the m constraints provide $n+m$ equations in $n+m$ variables (x_i 's and λ_j 's)
- Note: it is often useful to examine the functional forms of the lambdas – they are usually interesting.

Best Placement for repeaters



Staggering the inverters



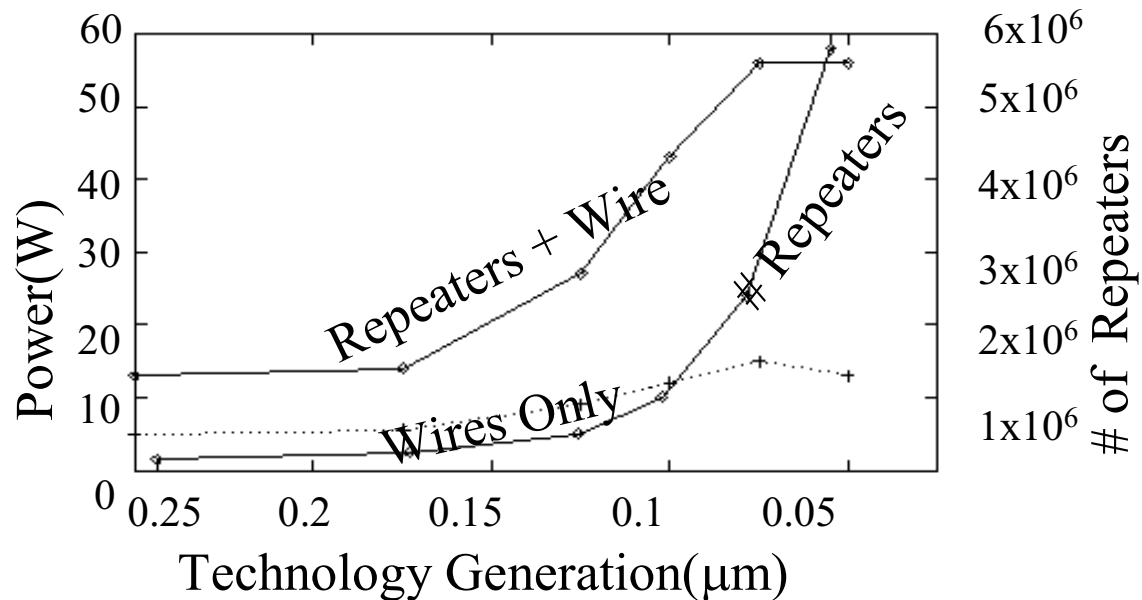
Avoiding the Miller cap by opposite going signals



Repeater Design Issues

- Delay-optimal repeaters are area and power hungry – use of sub-optimal insertion
- Optimal placement requires accurate modeling of interconnect.
- Optimal placement not always possible.
- Performance limited due to significant interconnect resistance.
- Source of noise – Supply and Substrate

With Scaling ...



- 1 million repeaters in a 100nm technology.
- Consuming about 30W (40%) in 100nm technology.
- Need to look at alternatives!!!

Differential Transmission

- Limiting swing saves significant amount of power.
- Rejects common-mode noise.
- Coupling is reduced due to dipole cancellation $O(n^3)$
- Doubled wire density --

